

# ON Semiconductor DATA SHEET

NPN Triple Diffused Planar Silicon Transistor

# **2SC4110** — 400V/25A Switching Regulator Applications

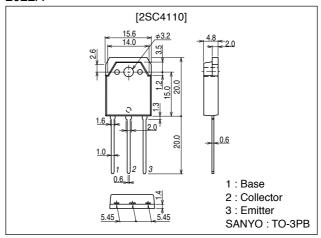
#### **Features**

- · High breakdown voltage and high reliability.
- · Fast switching speed.
- · Wide ASO.
- · Adoption of MBIT process.

### Package Dimensions

unit:mm

#### 2022A



## **Specifications**

#### Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	V <sub>CBO</sub>		500	V
Collector-to-Emitter Voltage	V <sub>CEO</sub>		400	V
Emitter-to-Base Voltage	V <sub>EBO</sub>		7	V
Collector Current	I <sub>C</sub>		25	Α
Collector Current (Pulse)	I <sub>CP</sub>	PW≤300μs, duty cycle≤10%	40	Α
Base Current	I <sub>B</sub>		8	Α
Collector Dissipation	В		2.5	W
	PC	Tc=25°C	160	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

#### Electrical Characteristics at Ta = 25°C

Parameter	Symbol	Conditions	Ratings			Linit
			min	typ	max	Unit
Collector Cutoff Current	I <sub>CBO</sub>	V <sub>CB</sub> =400V, I <sub>E</sub> =0			10	μΑ
Emitter Cutoff Current	I <sub>EBO</sub>	V <sub>EB</sub> =5V, I <sub>C</sub> =0			10	μΑ

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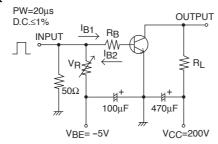
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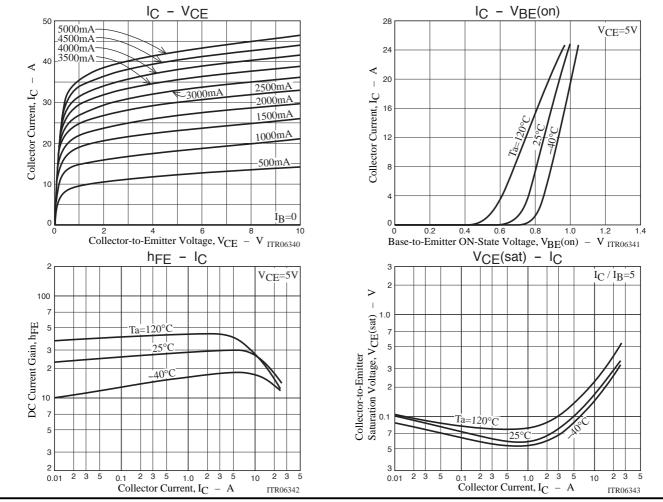
Parameter	Symbol	Conditions	Ratings			Unit
Farameter	Parameter Symbol Con-		min	typ	max	Offic
	h <sub>FE</sub> 1	V <sub>CE</sub> =5V, I <sub>C</sub> =3.2A			50*	
DC Current Gain	h <sub>FE</sub> 2	V <sub>CE</sub> =5V, I <sub>C</sub> =16A				
	h <sub>FE</sub> 3	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	10			
Collector-to-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =16A, I <sub>B</sub> =3.2A			0.8	V
Base-to-Emitter Saturation Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =16A, I <sub>B</sub> =3.2A			1.5	V
Gain-Bandwidth Product	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =3.2A		20		MHz
Output Capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, f=1MHz		300		pF
Collector-to-Base Breakdown Voltage	V <sub>(BR)</sub> CBO	I <sub>C</sub> =1mA, I <sub>E</sub> =0				V
Collector-to-Emitter Breakdown Voltage	V <sub>(BR)</sub> CEO	I <sub>C</sub> =10mA, R <sub>BE</sub> =∞				V
Emitter-to-Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =1mA, I <sub>C</sub> =0				V
Collector-to-Emitter Sustain Voltage	V <sub>CEX(sus)</sub>	I <sub>C</sub> =10A, I <sub>B1</sub> =1A, I <sub>B2</sub> =-4A, L=200 $\mu$ H, clamped				V
Turn-ON Time	ton	I <sub>C</sub> =20A, I <sub>B1</sub> =4A, I <sub>B2</sub> =-8A, R <sub>L</sub> =10Ω, V <sub>CC</sub> =200V			0.5	μs
Storage Time	t <sub>stg</sub>	I <sub>C</sub> =20A, I <sub>B1</sub> =4A, I <sub>B2</sub> =-8A, R <sub>L</sub> =10Ω, V <sub>CC</sub> =200V			2.5	μs
Fall Time	t <sub>f</sub>	I <sub>C</sub> =20A, I <sub>B1</sub> =4A, I <sub>B2</sub> =-8A, R <sub>L</sub> =10Ω, V <sub>CC</sub> =200V			0.3	μs

<sup>\*:</sup> The  $h_{FE}1$  of the 2SC4110 is classified as follows. When specifying the  $h_{FE}1$  rank, specify two ranks or more in principle.

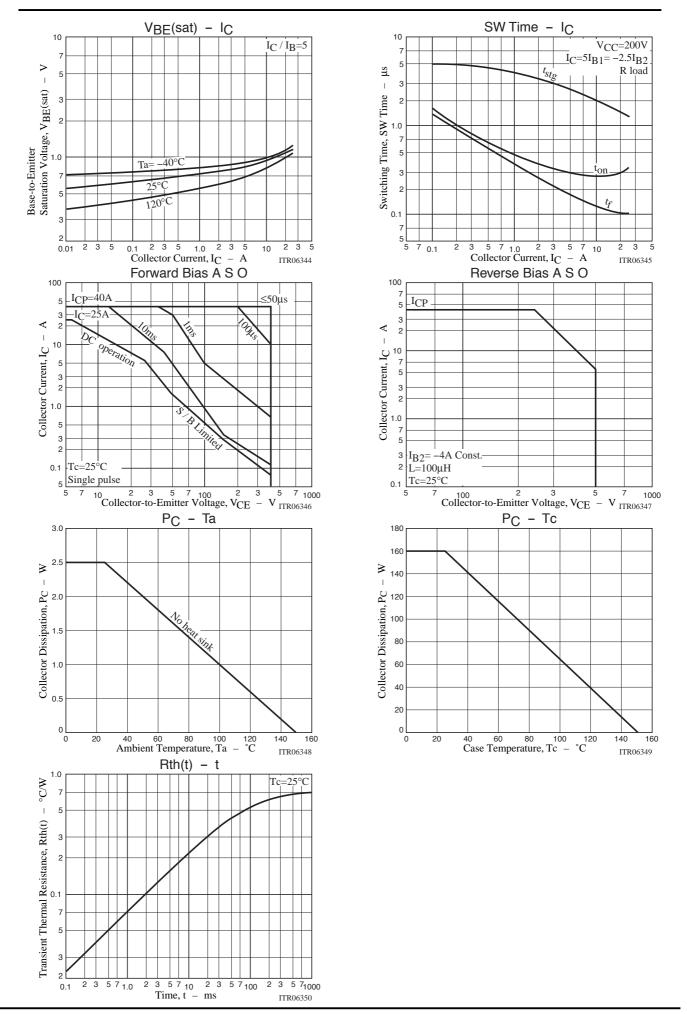
Rank	L	М	N		
hFE	15 to 30	20 to 40	30 to 50		

#### Switching Time Test Circuit





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#### 2SC4110

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